



Schottky Diodes



- High frequency operation
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Guard ring for enhanced ruggedness and long term reliability
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 ℃

Typical Applications

Typical applications are in switching power supplies, converters, freewheeling diodes, and reverse battery protection.

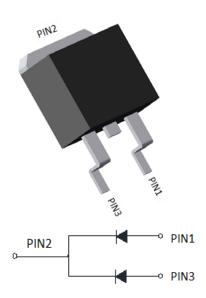
Mechanical Data

• Package: TO-263

Molding compound meets UL 94 V-0 flammability rating, RoHS-compliant

 Terminals: Tin plated leads, solderable per J-STD-002 and JESD22-B102

• Polarity: As marked



■Maximum Ratings (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	MBRBL30200CT
Device marking code			MBRBL30200CT
Repetitive Peak Reverse Voltage	VRRM	V	200
Average Rectified Output Current @60Hz sine wave, R-load, Ta (FIG 1)	Ю	Α	30
Surge(Non-repetitive)Forward Current @60Hz half sine-wave, 1 cycle, Ta=25°C	IFSM	Α	220
Current Squared Time @1ms≤t≤8.3ms Tj=25°C, rating of per diode	I2t	A2s	200
Storage Temperature	Tstg	°C	-55 ~ + 150
Junction Temperature	Tj	°C	-55 ~ + 150

■Electrical Characteristics (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	TEST CONDITIONS	MBRBL30200CT
Maximum instantaneous forward voltage drop per diode	VFM	V	IFM=15.0A	0.88
Maximum DC reverse current at rated DC blocking voltage per diode	IRRM1	mA	VRM=VRRM Ta=25°C	0.1
	IRRM2		VRM=VRRM Ta=100°C	20

■Thermal Characteristics (T_a=25°C Unless otherwise specified)

PAR	AMETER	SYMBOL	UNIT	MBRBL30200CT
Thermal Resistance	Between junction and case	R ₀ J-C	°CW	2.0

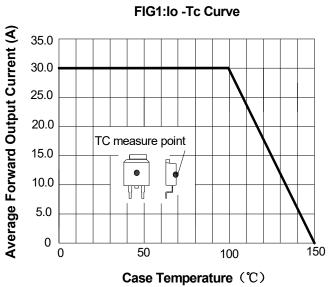


MBRBL30200CT

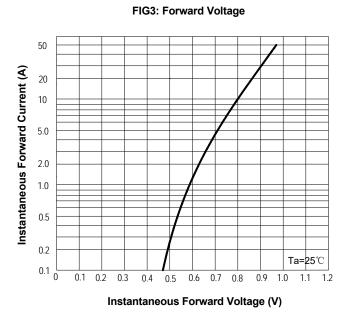
■Ordering Information (Example)

PREFERED P/N	UNIT WEIGHT(g)	MINIIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
MBRBL30200CT	Approximate 1.43	50	2000	8000	Tube
MBRBL30200CT	Approximate 1.43	1000	2000	10000	Reel

■Characteristics (Typical)



240 Peak Forward Surge Current (A) 200 160 120 80 40 0 2 5 **Number of Cycles**



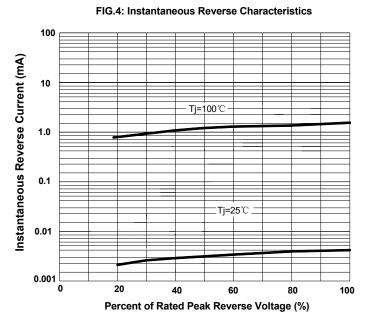


FIG2:Surge Forward Current Capability

10

20

8.3ms Single

Half Sine-Wave

EDEC Method

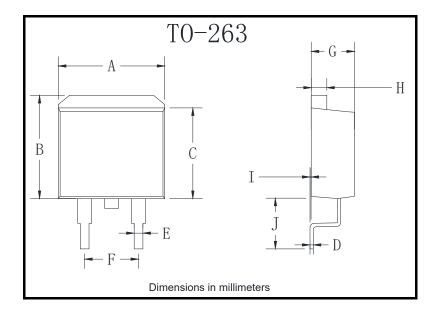
50

100





■Outline Dimensions



TO-263					
Dim	Min	Max			
Α	9.5	11.5			
В	9.7	10.5			
С	8.4	9.0			
D	0.28	0.64			
Е	0.68	0.94			
F	4.55	5.6			
G	4.04	5.10			
Н	1.14	1.4			
I	0	0.2			
J	4.9	6.05			



MBRBL30200CT

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